**TENTATIVE** 

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# **TC7WH125FU**

(UNDER DEVELOPMENT)

## **DUAL BUS BUFFER**

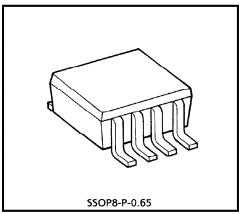
The TC7WH125 is an advanced high speed CMOS DUAL BUS BUFFERS fabricated with silicon gate CMOS technology.

They achieve the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The require 3-state control input  $\overline{G}$  to be set high to place the output into the impedance.

This device is designed to be used with 3-state memory address drivers, etc.

An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V system and two supply system such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.



Weight: 0.02g (Typ.)

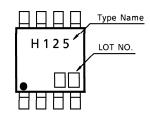
#### **FEATURES**

- High Speed  $t_{pd} = 3.8$ ns (Typ.) at  $V_{CC} = 5V$
- Low Power Dissipation ......  $I_{CC} = 2\mu A$  (Max.) at Ta = 25°C
- High Noise Immunity .....  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays ······ t<sub>pLH</sub> ≒t<sub>pHL</sub>
- Wide Operation Voltage Range… V<sub>CC</sub> (opr) = 2~5.5V
- Low Noise ...... V<sub>OLP</sub> = 0.8V (Max.)

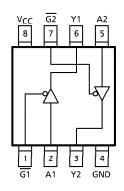
## **MAXIMUM RATINGS** (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	Vcc	-0.5~7	V
DC Input Voltage	VIN	-0.5~7	V
DC Output Voltage	VOUT	-0.5~V <sub>CC</sub> +0.5	V
Input Diode Current	Ικ	- 20	mA
Output Diode Current	loк	± 20	mA
DC Output Current	lout	± 25	mΑ
DC V <sub>CC</sub> / Ground Current	lcc	± 50	mA
Power Dissipation	PD	300	mW
Storage Temperature	T <sub>stg</sub>	<b>-65∼150</b>	°C
Lead Temperature (10 s)	TL	260	°C

#### **MARKING**



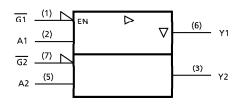
#### PIN ASSIGNMENT (TOP VIEW)



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## **LOGIC DIAGRAM**



## TRUTH TABLE

INPUTS		OUTPUTS
G	Α	Υ
Н	×	Z
L	L	L
L	Н	Н

x : Don't Care Z : High Impedance

## RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Supply Voltage	Vcc	2~5.5	V	
Input Voltage	VIN	0~5.5	٧	
Output Voltage	VOUT	0~V <sub>CC</sub>	٧	
Operating Temperature	T <sub>opr</sub>	<b>- 40∼85</b>	°C	
Input Rise and Fall Time	dt / dv	$0\sim100 \text{ (V}_{CC}=3.3\pm0.3\text{V)}$	nc	
	dt/dv	$0\sim20 \ (V_{CC} = 5 \pm 0.5V)$	ns	

#### DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC SYMBOL		TEST CONDITION		Vcc	Ta = 25°C			Ta = −40~85°C		UNIT	
CHARACTERISTIC	STIVIBUL	1231 CONDITION		(V)	MIN.	TYP.	MAX.	MIN.	MAX.	CIVII	
High-Level				2.0	1.5	_	_	1.5	_		
Input Voltage	V <sub>IH</sub>	_		3.0~ 5.5	∨ <sub>CC</sub> ×0.7	_	_	V <sub>C</sub> C ×0.7	_	٧	
Lave Lavel				2.0	_	_	0.5	_	0.5		
Low-Level Input Voltage	VIL	_		3.0~ 5.5	_	_	V <sub>C</sub> C × 0.3	_	V <sub>C</sub> C × 0.3	V	
				2.0	1.9	2.0	_	1.9		V	
I limb I aval		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -50 \mu A$	3.0	2.9	3.0	_	2.9	_		
High-Level Output Voltage	Voн			4.5	4.4	4.5	_	4.4			
Output Voltage			$I_{OH} = -4mA$	3.0	2.58	_	_	2.48	_		
			$I_{OH} = -8mA$	4.5	3.94	_	<b>—</b>	3.8	_		
		V <sub>IN</sub> = V <sub>IL</sub>	I <sub>OL</sub> = 50μA	2.0		0.0	0.1	_	0.1	V	
Low-Level				3.0	_	0.0	0.1	_	0.1		
Output Voltage	$v_{OL}$			4.5	_	0.0	0.1	_	0.1		
Catput Voltage			$I_{OL} = 4mA$	3.0			0.36	_	0.44		
			I <sub>OL</sub> = 8mA	4.5	_		0.36	_	0.44		
3-State Output Off-State Current	loz	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>OUT</sub> = V <sub>CC</sub> or GND		5.5	_	-	± 0.25	_	± 2.5	$\mu$ A	
Input Leakage Current	IIN	V <sub>IN</sub> = V <sub>CC</sub> or GND		0~ 5.5	_	_	± 0.1	_	± 1.0	μΑ	
Quiescent Supply Current	lcc	V <sub>IN</sub> =V <sub>CC</sub> or GND		5.5	_	_	2.0	_	20.0	μΑ	

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# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$ )

CHADACTERISTIC	SYMBOL	TEST CONDITION		Ta = 25°C			Ta = -4	UNIT		
CHARACTERISTIC	STIVIBUL		V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
			3.3 ± 0.3	15		5.6	8.0	1.0	9.5	
Propagation Delay	t <sub>pLH</sub>			50		8.1	11.5	1.0	13.0	
Time	tpHL		5.0 ± 0.5	15	_	3.8	5.5	1.0	6.5	ns
			3.0 ± 0.5	50	_	5.3	7.5	1.0	8.5	
		$R_L = 1k\Omega$	3.3 ± 0.3	15		5.4	8.0	1.0	9.5	ns
3-State Output	<sup>t</sup> pZL <sup>t</sup> pZH			50		7.9	11.5	1.0	13.0	
Enable Time			5.0 ± 0.5	15		3.6	5.1	1.0	6.0	
				50		5.1	7.1	1.0	8.0	
3-State Output	t <sub>pLZ</sub>	$R_{I} = 1k\Omega$	3.3 ± 0.3	50	_	9.5	13.2	1.0	15.0	ns
Disable Time	t <sub>pHZ</sub>	KC = 1K22	5.0 ± 0.5	50		6.1	8.8	1.0	10.0	ns
Output to Output	tosLH	(Note 1)	3.3 ± 0.3	50	_	_	1.5	_	1.5	ne
Skew	tosHL	(Note I)	5.0 ± 0.5	50		_	1.0	_	1.0	ns
Input Capacitance	CIN				_	4	10	_	10	рF
Output Capacitance	COUT		·			6	_		_	рF
Power Dissipation Capacitance (Note 2)	C <sub>PD</sub>					14			_	pF

(Note 1) : Parameter guaranteed by design.  $t_{OSLH} = |t_{pLHm} - t_{pLHn}| \setminus t_{OSHL} = |t_{pHLm} - t_{pHLn}|$  (Note 2) : CpD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation :

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2$  (per bit)

# **NOISE CHARACTERISTICS** (Ta = 25°C, Input $t_f = t_f = 3ns$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	V <sub>CC</sub> (V)	TYP.	LIMIT	UNIT
Quiet Output Maximum Dynamic V <sub>OL</sub>	V <sub>OLP</sub>	C <sub>L</sub> = 50pF	5.0	0.5	0.8	V
Quiet Output Minimum Dynamic V <sub>OL</sub>	V <sub>OLV</sub>	C <sub>L</sub> = 50pF	5.0	- 0.5	-0.8	V
Minimum High Level Dynamic Input Voltage	V <sub>IHD</sub>	C <sub>L</sub> = 50pF	5.0	_	3.5	V
Maximum Low Level Dynamic Input Voltage	V <sub>ILD</sub>	C <sub>L</sub> = 50pF	5.0		1.5	V

# INPUT EQUIVALENT CIRCUIT

